SGS-THOMSON MICROELECTRONICS

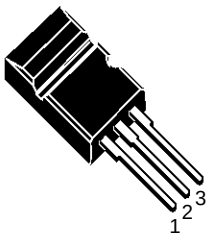
STU6NA90

N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STU6NA90	900 V	< 2 Ω	5.8 A

- TYPICAL $R_{DS(on)}$ = 1.5 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- REPETITIVE AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

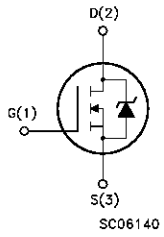


Max220™

DESCRIPTION

The Max220™ package is a new high volume power package exibiting the same footprint as the industry standard TO-220, but designed to accomodate much larger silicon chips, normally supplied in bigger packages. The increased die capacity makes the device ideal to reduce component count in multiple paralleled TO-220 designs and save board space with respect to larger packages.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES (UPS)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	900	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	900	V
V_{GS}	Gate-source Voltage	± 30	V
I_D	Drain Current (continuous) at T_c = 25 °C	5.8	A
I_D	Drain Current (continuous) at T_c = 100 °C	3.7	A
I_{DM}(•)	Drain Current (pulsed)	23.2	A
P_{tot}	Total Dissipation at T_c = 25 °C	145	W
	Derating Factor	1.16	W/°C
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.86	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	30	°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.1	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	6	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 50$ V)	180	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	7.2	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100\ ^oC$, pulse width limited by T_j max, $\delta < 1\%$)	3.8	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$	900			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 $T_c = 125\ ^oC$			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30$ V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	2.25	3	3.75	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10$ V $I_D = 3$ A $V_{GS} = 10$ V $I_D = 3$ A $T_c = 100^oC$		1.5	2 4	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	6			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 3$ A	5	6.6		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V f = 1 MHz $V_{GS} = 0$		1770 190 50	2300 250 70	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 450 V I_D = 3 A R_G = 4.7 Ω V_{GS} = 10 V		27 30	40 45	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	V_{DD} = 720 V I_D = 6 A R_G = 47 Ω V_{GS} = 10 V		110		A/µs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 720 V I_D = 6 A V_{GS} = 10 V		72 10 34	105	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 720 V I_D = 6 A R_G = 4.7 Ω V_{GS} = 10 V		18 7 31	27 12 47	ns ns ns

SOURCE DRAIN DIODE

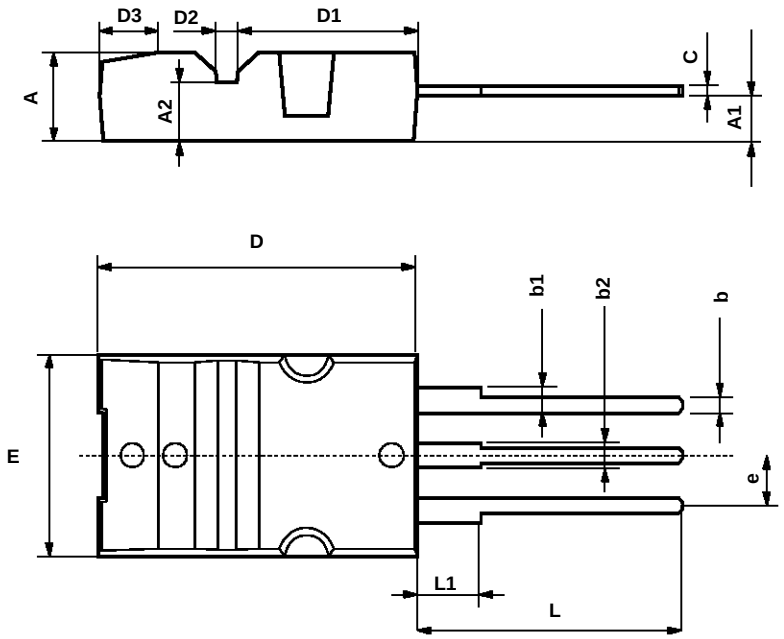
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				5.8 23.2	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 6 A V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 6 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		830 13.7 33		ns µC A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

Max220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.3		4.6	0.169		0.181
A1	2.2		2.4	0.087		0.094
A2	2.9		3.1	0.114		0.122
b	0.7		0.93	0.027		0.036
b1	1.25		1.4	0.049		0.055
b2	1.2		1.38	0.047		0.054
c	0.45		0.6		0.18	0.023
D	15.9		16.3		0.626	0.641
D1	9		9.35	0.354		0.368
D2	0.8		1.2	0.031		0.047
D3	2.8		3.2	0.110		0.126
e	2.44		2.64	0.096		0.104
E	10.05		10.35	0.396		0.407
L	13.2		13.6	0.520		0.535
L1	3		3.4	0.118		0.133



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